TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# **TC74LCX16373FT**

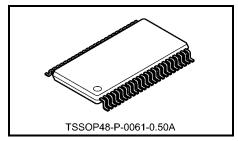
#### Low-Voltage 16-Bit D-Type Latch with 5-V Tolerant Inputs and Outputs

The TC74LCX16373FT is a high-performance CMOS 16-bit D-type latch. Designed for use in 2.5-V or 3.3-V systems, it achieves high-speed operation while maintaining the CMOS low power dissipation.

The device is designed for low-voltage (2.5-V or 3.3-V) V<sub>CC</sub> applications, but it could be used to interface to 5-V supply environment for both inputs and outputs.

This 16-bit D-type latch is controlled by a latch enable input (LE) and an output enable input ( $\overline{OE}$ ) which are common to each byte. It can be used as two 8-bit latches or one 16-bit latch. When the  $\overline{OE}$  input is high, the outputs are in a high-impedance state.

All inputs are equipped with protection circuits against static discharge.

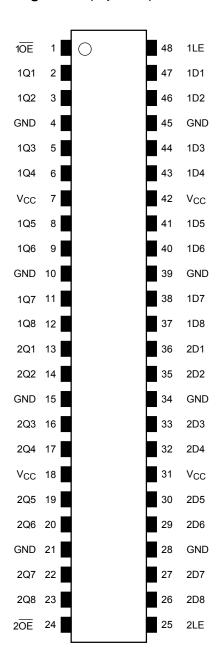


Weight: 0.25 g (typ.)

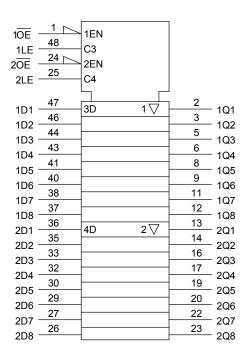
#### **Features**

- Low-voltage operation: V<sub>CC</sub> = 2.0 to 3.6 V
- High-speed operation:  $t_{pd} = 5.4 \text{ ns (max) (V}_{CC} = 3.0 \text{ to } 3.6 \text{ V})$
- Ouput current:  $|I_{OH}|/I_{OL} = 24 \text{ mA (min)} (V_{CC} = 3.0 \text{ V})$
- Latch-up performance: -500 mA
- Package: TSSOP
- Power-down protection provided on all inputs and outputs

#### Pin Assignment (top view)



## **IEC Logic Symbol**



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#### **Truth Table**

	Outputs		
1OE	1LE	1D1-1D8	1Q1-1Q8
Н	Х	Х	Z
L	L	Х	Qn
L	Н	L	L
L	Н	Н	Н

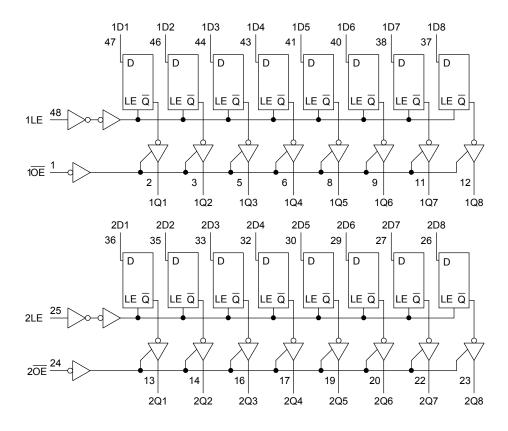
	Outputs		
2 <del>OE</del>	2LE	2D1-2D8	2Q1-2Q8
Н	Х	Х	Z
L	L	Х	Qn
L	Н	L	L
L	Н	Н	Н

X: Don't care

Z: High impedance

Qn: Q outputs are latched at the time when the LE input is taken to a low logic level

## **System Diagram**





#### **Absolute Maximum Ratings (Note 1)**

Characteristics	Symbol	Rating	Unit
Power supply voltage	V <sub>CC</sub>	−0.5 to 6.0	V
Input voltage	$V_{IN}$	-0.5 to 7.0	V
Output voltage	Vout	-0.5 to 7.0 (Note 2)	V
Output voltage	VOU1	-0.5 to V <sub>CC</sub> + 0.5 (Note 3)	V
Input diode current	I <sub>IK</sub>	-50	mA
Output diode current	lok	±50 (Note 4)	mA
DC output current	I <sub>OUT</sub>	±50	mA
Power dissipation	$P_{D}$	400	mW
DC V <sub>CC</sub> /ground current per supply pin	I <sub>CC</sub> /I <sub>GND</sub>	±100	mA
Storage temperature	T <sub>stg</sub>	-65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: Output in OFF state

Note 3: High or low state. IOUT absolute maximum rating must be observed.

Note 4: Vout < GND, Vout > Vcc

### **Operating Ranges (Note 1)**

Characteristics	Symbol	Rating	Unit
Power supply voltage	V <sub>CC</sub>	2.0 to 3.6	V
Tower supply voltage	VCC	1.5 to 3.6 (Note 2)	V
Input voltage	V <sub>IN</sub>	0 to 5.5	V
Output voltage	V <sub>OUT</sub>	0 to 5.5 (Note 3)	V
Output voltage	VOU1	0 to V <sub>CC</sub> (Note 4)	V
		±24 (Note 5)	
Output current	I <sub>OH</sub> /I <sub>OL</sub>	±12 (Note 6)	mA
		±8 (Note 7)	
Operating temperature	T <sub>opr</sub>	-40 to 85	°C
Input rise and fall time	dt/dv	0 to 10 (Note 8)	ns/V

Note 1: The operating ranges must be maintained to ensure the normal operation of the device.

Unused inputs must be tied to either VCC or GND.

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Note 2: Data retention only

Note 3: Output in OFF state

Note 4: High or low state

Note 5:  $V_{CC} = 3.0 \text{ to } 3.6 \text{ V}$ 

Note 6:  $V_{CC} = 2.7 \text{ to } 3.0 \text{ V}$ 

Note 7:  $V_{CC} = 2.3 \text{ to } 2.7 \text{ V}$ 

Note 8:  $V_{IN} = 0.8$  to 2.0 V,  $V_{CC} = 3.0$  V



## **Electrical Characteristics**

## DC Characteristics ( $Ta = -40 \text{ to } 85^{\circ}\text{C}$ )

Characteristics		Symbol	ol Test Condition		1	Min	Max	Unit
		-,	, 551, 551, 61, 61		V <sub>CC</sub> (V)		Max	O
	H-level	\/			2.3 to 2.7	1.7	_	
Input voltage	n-ievei	VIH	-		2.7 to 3.6	2.0	_	V
iliput voltage	L-level				2.3 to 2.7	_	0.7	
	L-ievei	V <sub>IL</sub>	-	_	2.7 to 3.6	_	0.8	
				I <sub>OH</sub> = -100 μA	2.3 to 3.6	V <sub>CC</sub> - 0.2	_	
				$I_{OH} = -8 \text{ mA}$	2.3	1.8	_	
	H-level	Voн	$V_{IN} = V_{IH}$ or $V_{IL}$	I <sub>OH</sub> = -12 mA	2.7	2.2		V
				I <sub>OH</sub> = -18 mA	3.0	2.4	_	
Output voltage				I <sub>OH</sub> = -24 mA	3.0	2.2	_	
			$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OL} = 100 \mu A$	2.3 to 3.6	_	0.2	
				I <sub>OL</sub> = 8 mA	2.3	_	0.6	
	L-level	V <sub>OL</sub>		I <sub>OL</sub> = 12 mA	2.7	_	0.4	
					I <sub>OL</sub> = 16 mA	3.0	_	0.4
				I <sub>OL</sub> = 24 mA	3.0	_	0.55	
Input leakage current		I <sub>IN</sub>	V <sub>IN</sub> = 0 to 5.5 V		2.3 to 3.6	_	±5.0	μА
2 state sutput OFF sta	ata auremant		$V_{IN} = V_{IH}$ or $V_{IL}$	$V_{IN} = V_{IH}$ or $V_{IL}$	/ <sub>IH</sub> or V <sub>IL</sub>		15.0	
3-state output OFF state current		loz	$V_{OUT} = 0$ to 5.5 V		2.3 to 3.6		±5.0	μΑ
Power-off leakage cur	rent	l <sub>OFF</sub>	V <sub>IN</sub> /V <sub>OUT</sub> = 5.5 V		0		10.0	μΑ
Quiescent supply curr	ent .	Icc	V <sub>IN</sub> = V <sub>CC</sub> or GND	V <sub>IN</sub> = V <sub>CC</sub> or GND			20.0	
Quiescent supply cum	Quiescent supply current		$V_{IN}/V_{OUT} = 3.6 \text{ to } 5.5$	<sub>OUT</sub> = 3.6 to 5.5 V		_	±20.0	μΑ
Increase in Icc per inp	ut	Δlcc	$V_{IH} = V_{CC} - 0.6 V$		2.3 to 3.6	ĺ	500	



## AC Characteristics ( $Ta = -40 \text{ to } 85^{\circ}\text{C}$ )

Characteristics	Symbol	/mbol Test Condition			Min	Max	Unit
Characteristics	Syllibol	rest Condition	V <sub>CC</sub> (V)	CL(pF)	IVIIII	IVIAX	Offic
Propagation delay time	<b>+</b>		$2.5\pm0.2$	30	1.5	6.5	
(D-Q)	t <sub>pLH</sub>	Figure 1, Figure 2	2.7	50	1.5	5.9	ns
(D-Q)	t <sub>pHL</sub>		$3.3 \pm 0.3$	50	1.5	5.4	
Dranagation dalay time	4		$2.5\pm0.2$	30	1.5	6.6	
Propagation delay time (LE-Q)	t <sub>pLH</sub>	Figure 1, Figure 2	2.7	50	1.5	6.4	ns
(LE-Q)	t <sub>pHL</sub>		$3.3 \pm 0.3$	50	1.5	5.5	
	4		$2.5\pm0.2$	30	1.5	7.9	
3-state output enable time	t <sub>pZL</sub>	Figure 1, Figure 3	2.7	50	1.5	6.5	ns
	t <sub>pZH</sub>		$3.3 \pm 0.3$	50	1.5	6.1	
		Figure 1, Figure 3	$2.5\pm0.2$	30	1.5	7.2	ns
3-state output disable time	t <sub>pLZ</sub>		2.7	50	1.5	6.3	
	t <sub>pHZ</sub>		$3.3 \pm 0.3$	50	1.5	6.0	
		Figure 1, Figure 2	$2.5\pm0.2$	30	3.5	_	
Minimum pulse width (LE)	t <sub>w</sub> (H)		2.7	50	3.0	_	ns
(LE)			$3.3 \pm 0.3$	50	3.0	_	
			$2.5\pm0.2$	30	3.0	_	
Minimum setup time	ts	Figure 1, Figure 2	2.7	50	2.5	_	ns
			$3.3 \pm 0.3$	50	2.5	_	
			$2.5\pm0.2$	30	2.0	_	
Minimum hold time	t <sub>h</sub>	Figure 1, Figure 2	2.7	50	1.5	_	ns
			$3.3\pm0.3$	50	1.5	_	
	4		$2.5\pm0.2$	30	_	_	
Output to output skew	t <sub>osLH</sub>	(Note)	2.7	50	_	_	ns
	tosHL		$3.3\pm0.3$	50		1.0	

Note: Parameter guaranteed by design.

 $(t_{OSLH} = |t_{pLHm} - t_{pLHn}|, t_{OSHL} = |t_{pHLm} - t_{pHLn}|)$ 

## **Dynamic Switching Characteristics**

(Ta = 25°C, input:  $t_r = t_f = 2.5 \text{ ns}, R_L = 500 \Omega$ )

Characteristics	Symbol	Test Condition	V <sub>CC</sub> (V)	Тур.	Unit
Quiet output maximum	V <sub>OLP</sub>	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}, C_L = 30 \text{pF}$	2.5	0.6	V
dynamic V <sub>OL</sub>	VOLP	$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}, C_L = 50 \text{pF}$	3.3	8.0	V
Quiet output minimum	IV.	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}, C_L = 30 \text{pF}$	2.5	0.6	V
dynamic V <sub>OL</sub>	V <sub>OLV</sub>	V <sub>IH</sub> = 3.3 V, V <sub>IL</sub> = 0 V, C <sub>L</sub> =50pF	3.3	8.0	V



## **Capacitive Characteristics (Ta = 25°C)**

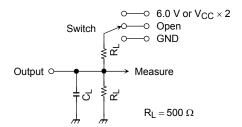
Characteristics	Symbol	Test Condition		V <sub>CC</sub> (V)	Тур.	Unit
Input capacitance	C <sub>IN</sub>	_		3.3	7	pF
Output capacitance	C <sub>OUT</sub>	_		3.3	8	pF
Power dissipation capacitance	C <sub>PD</sub>	$f_{IN} = 10 \text{ MHz}$	lote)	3.3	25	pF

Note: CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/16 \text{ (per bit)}$ 

#### **AC Test Circuit**



Parameter	Switch			
t <sub>pLH</sub> , t <sub>pHL</sub>	Open			
t <sub>pLZ</sub> , t <sub>pZL</sub>	$ \begin{array}{lll} 6.0 \ V & @V_{CC} = 3.3 \pm 0.3 \ V \\ V_{CC} \times 2 & @V_{CC} = 2.5 \pm 0.2 \ V \\ \end{array} $			
t <sub>pHZ</sub> , t <sub>pZH</sub>	GND			

Figure 1

#### **AC Waveform**

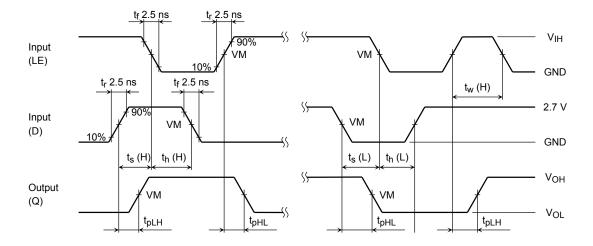


Figure 2  $t_{pLH}$ ,  $t_{pHL}$ ,  $t_w$ ,  $t_s$ ,  $t_h$ 

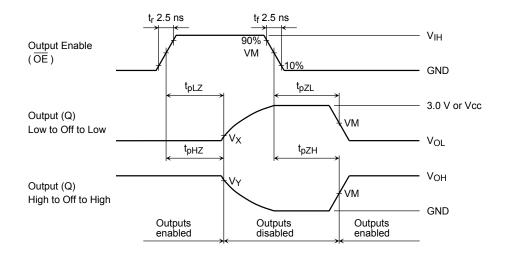


Figure 3  $t_{pLZ}$ ,  $t_{pHZ}$ ,  $t_{pZL}$ ,  $t_{pZH}$ 

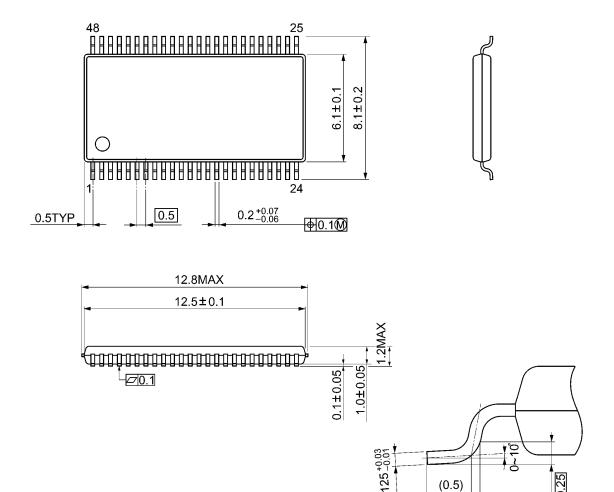
Symbol		V <sub>CC</sub>	
Symbol	$3.3\pm0.3~\textrm{V}$	2.7 V	$2.5\pm0.2\textrm{V}$
V <sub>IH</sub>	2.7 V	2.7 V	V <sub>CC</sub>
V <sub>M</sub>	1.5 V	1.5 V	V <sub>CC</sub> /2
VX	V <sub>OL</sub> + 0.3 V	V <sub>OL</sub> + 0.3 V	V <sub>OL</sub> + 0.15 V
VY	V <sub>OH</sub> – 0.3 V	V <sub>OH</sub> – 0.3 V	V <sub>OH</sub> – 0.15 V

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## **Package Dimensions**

TSSOP48-P-0061-0.50A

Unit: mm



Weight: 0.25 g (typ.)

0.45~0.75

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20070701-EN GENERAL

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